1. General description

NPN high-voltage low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability $\rm I_{C}$ and $\rm I_{CM}$
- High collector current gain (hFE) at high IC
- AEC-Q101 qualified
- Small SMD plastic package

3. Applications

- · LED driver for LED chain module
- LCD backlighting
- Automotive power management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	180	V
I _C	collector current		-	-	1	Α
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	250	-	



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5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol
В	base	3	С
Е	emitter		j
С	collector	- 	В —
			 E
		1	sym021
	B E	B base E emitter	B base E emitter C collector

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV8118T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV8118T	LZ%

[1] % = placeholder for manufacturing site code

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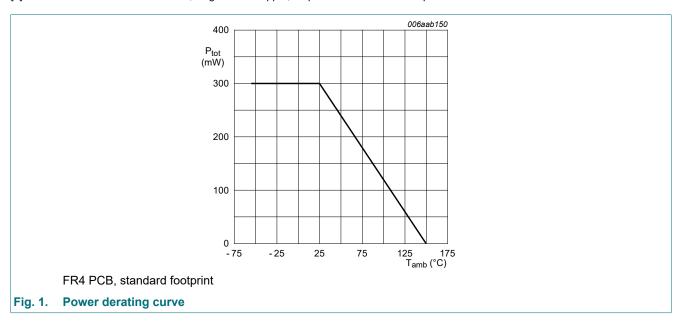
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	400	V
V _{CEO}	collector-emitter voltage	open base		-	180	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _{BM}	peak base current			-	400	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



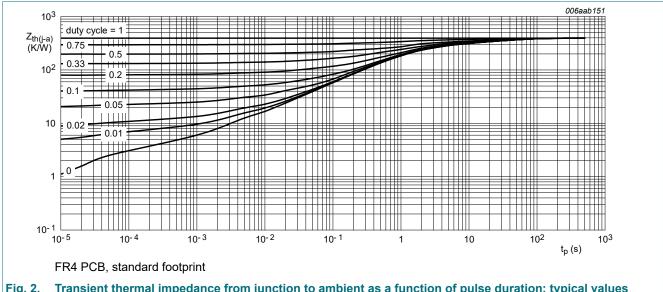
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 144 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 144 V; I _E = 0 A; T _j = 150 °C	-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 144 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 50 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	250	-	
		V_{CE} = 10 V; I_{C} = 100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	250	-	
		V_{CE} = 10 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	100	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 100 mA; I_B = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	40	60	mV
		I_C = 100 mA; I_B = 20 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	33	50	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 0.5 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1	1.2	V
t _d	delay time	$V_{CC} = 6 \text{ V}; I_C = 0.5 \text{ A}; I_{Bon} = 0.1 \text{ A};$	-	7	-	ns
t _r	rise time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	565	-	ns
t _{on}	turn-on time		-	572	-	ns
t _s	storage time		-	1320	-	ns
t _f	fall time		-	740	-	ns
t _{off}	turn-off time		-	2060	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	-	30	-	MHz
C _c	collector capacitance	V_{CB} = 20 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	5.7	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	150	-	pF

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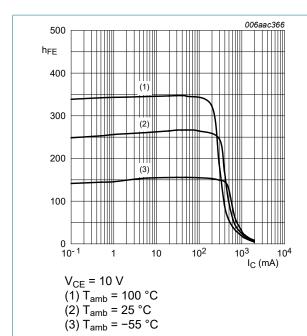


Fig. 3. DC current gain as a function of collector current; typical values

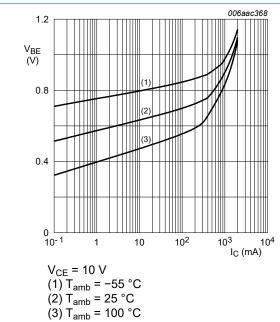


Fig. 5. Base-emitter voltage as a function of collector current; typical values

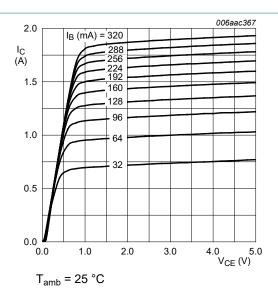
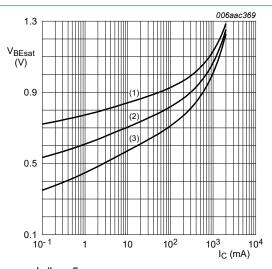


Fig. 4. Collector current as a function of collectoremitter voltage; typical values



 $I_{C}/I_{B} = 5$ (1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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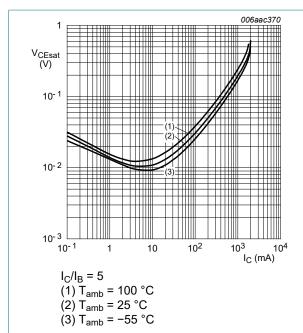


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

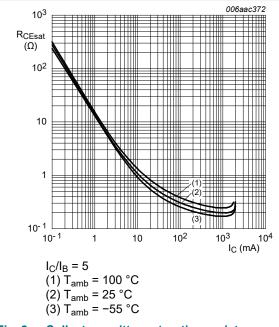


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

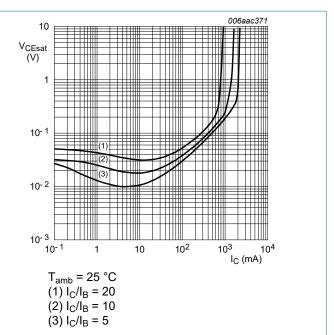


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

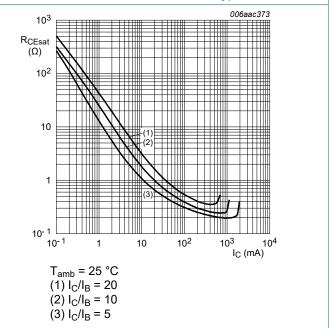
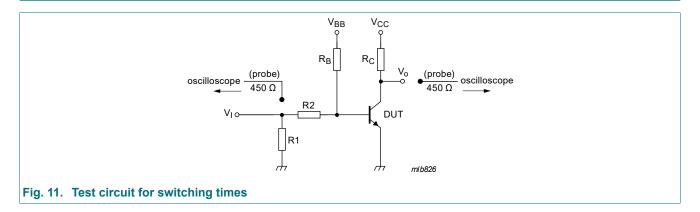


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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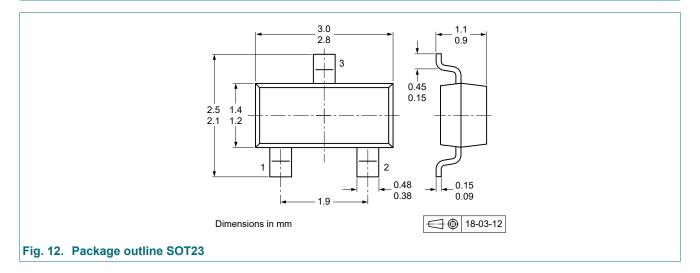
11. Test information



Quality information

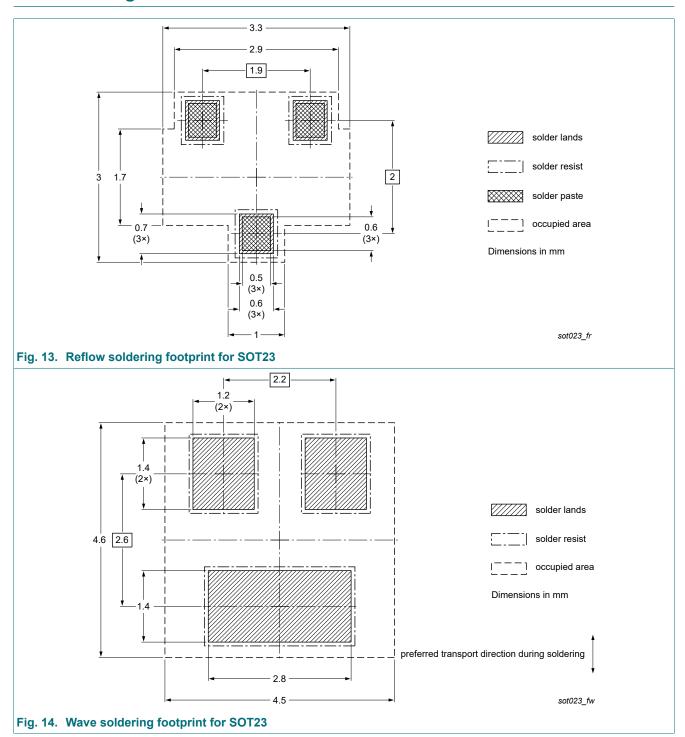
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBHV8118T v.2	20230712	Product data sheet	-	PBHV8118T v.1				
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 							
PBHV8118T v.1	20100507	Product data sheet	-	-				

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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